Description

N-channel Enhancement Mode Power MOSFET

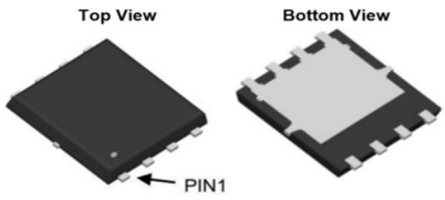
Features

- 60V, 40A
  $R_{DS(ON)}$ Typ= 12mΩ @ V_{GS} = 10V
  $R_{DS(ON)}$ Typ= 16mΩ @ V_{GS} = 4.5V
- Advanced Trench Technology
- Excellent $R_{DS(ON)}$ and Low Gate Charge

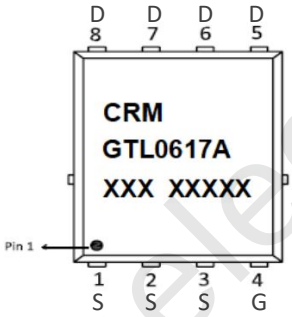
Applications

- Load Switch
- PWM Application
- Power Management

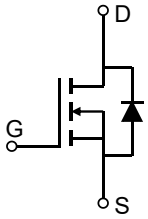
100% UIS TESTED!
100% ΔVds TESTED!



PDFN5x6-8L



Marking and Pin Assignment



Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	Outline	Package	Reel Size	Reel(pcs)	Per Carton (pcs)
CRMGTL0617A	CRMGTL0617A	TAPING	PDFN5x6-8L	13"	5000	50000

Absolute Maximum Ratings (@ T_C = 25°C unless otherwise specified)

Symbol	Parameter		Value	Units
V_{DS}	Drain-to-Source Voltage		60	V
V_{GS}	Gate-to-Source Voltage		±20	V
I_D	Continuous Drain Current	T_C = 25°C	40	A
		T_C = 100°C	26	
I_{DM}	Pulsed Drain Current (1)		160	A
E_{AS}	Single Pulsed Avalanche Energy (2)		72	mJ
P_D	Power Dissipation	T_C = 25°C	42	W
$R_{\theta JC}$	Thermal Resistance, Junction to Ambient		3	°C/W
T_J, T_{STG}	Junction & Storage Temperature Range		-55 to 150	°C

Electrical Characteristics (T_J = 25°C unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	I_D = 250μA, V_{GS} = 0V	60	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 60V, V_{GS} = 0V	-	-	1.0	μA
I_{GSS}	Gate-Body Leakage Current	V_{DS} = 0V, V_{GS} = ±20V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250μA	1	1.5	2.2	V
$R_{DS(ON)}$	Static Drain-Source ON-Resistance(3)	V_{GS} = 10V, I_D = 30A	-	12	15	mΩ
		V_{GS} = 4.5V, I_D = 20A	-	16	21	mΩ
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{GS} = 0V, V_{DS} = 25V, f = 1MHz	-	2030	-	pF
C_{oss}	Output Capacitance		-	133	-	pF
C_{rss}	Reverse Transfer Capacitance		-	122	-	pF
Q_g	Total Gate Charge	V_{GS} = 0 to 10V, V_{DS} = 30V, I_D = 30A	-	45	-	nC
Q_{gs}	Gate Source Charge		-	8	-	nC
Q_{gd}	Gate Drain("Miller") Charge		-	11	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-On DelayTime	V_{GS} = 10V, V_{DD} = 30V, I_D= 30A, R_{GEN} = 1.8Ω	-	11	-	ns
t_r	Turn-On Rise Time		-	79	-	ns
$t_{d(off)}$	Turn-Off DelayTime		-	33	-	ns
t_f	Turn-Off Fall Time		-	107	-	ns
Drain-Source Diode Characteristics and Max Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	40	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	160	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS} = 0V, I_S = 30A	-	-	1.2	V

Notes: 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.

2. E_{AS} condition: Starting T_J=25C, V_{DD}=30V, V_G=10V, R_G=25ohm, L=0.5mH, I_{AS}=17A

3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%.

Typical Performance Characteristics

Figure 1: Output Characteristics

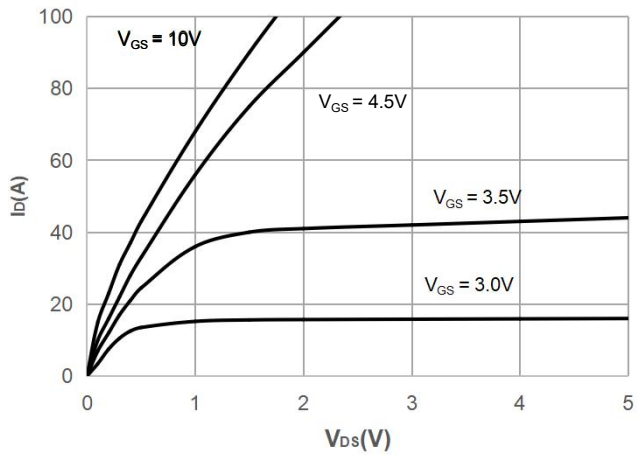


Figure 2: Typical Transfer Characteristics

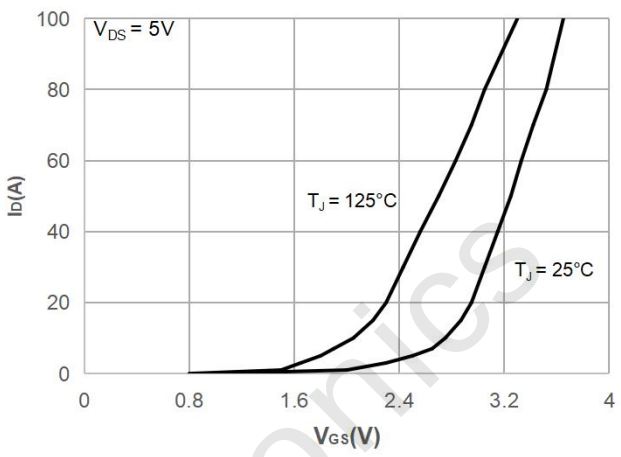


Figure 3: On-resistance vs. Drain Current

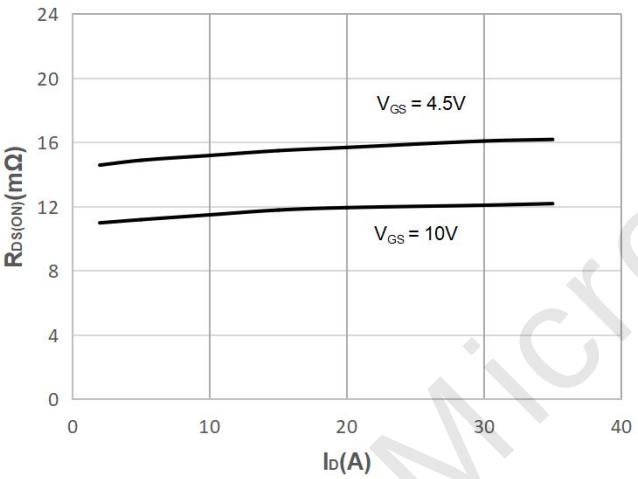


Figure 4: Body Diode Characteristics

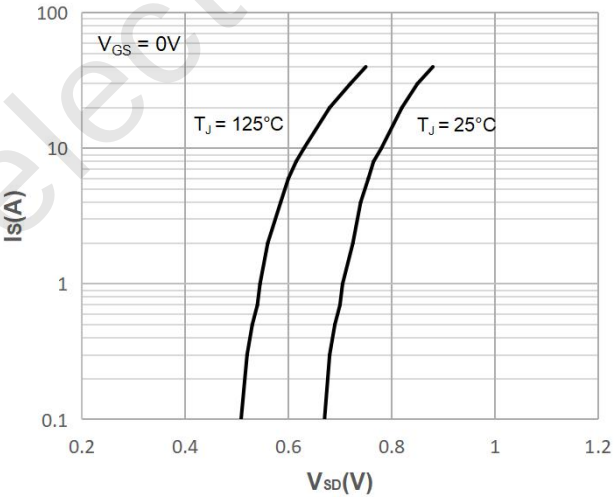


Figure 5: Gate Charge Characteristics

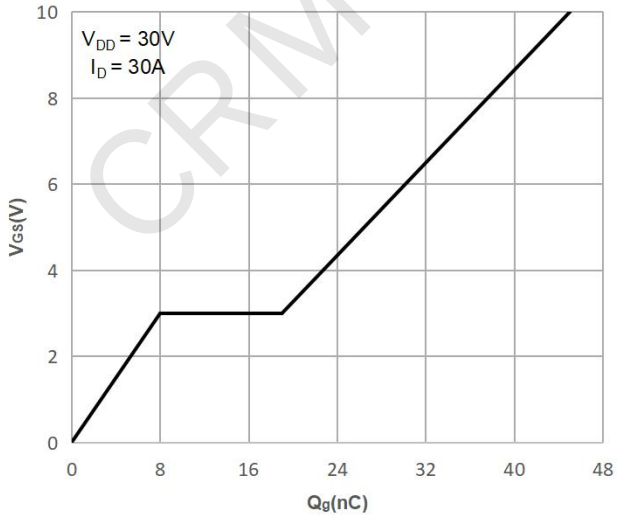
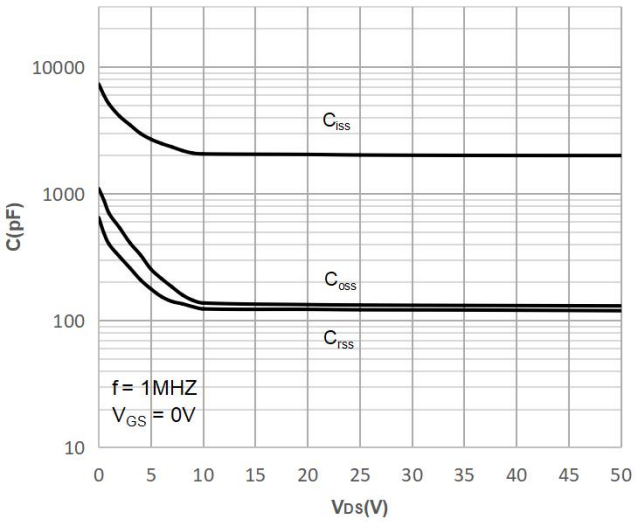


Figure 6: Capacitance Characteristics



Typical Performance Characteristics

Figure 7: Normalized Breakdown voltage vs. Junction Temperature

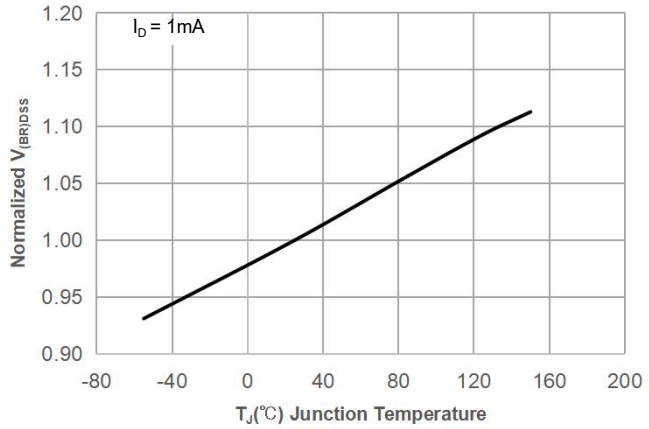


Figure 8: Normalized on Resistance vs. Junction Temperature

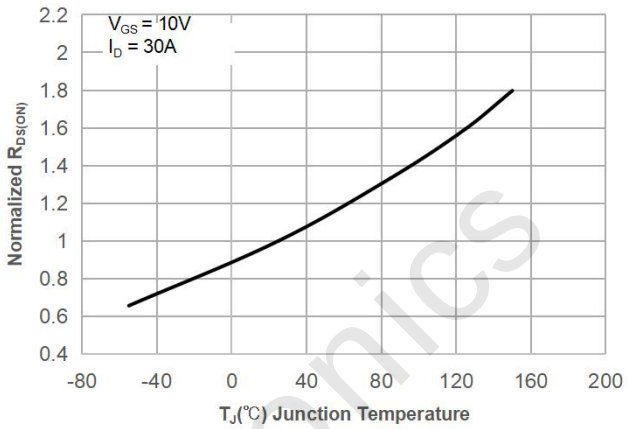


Figure 9: Maximum Safe Operating Area

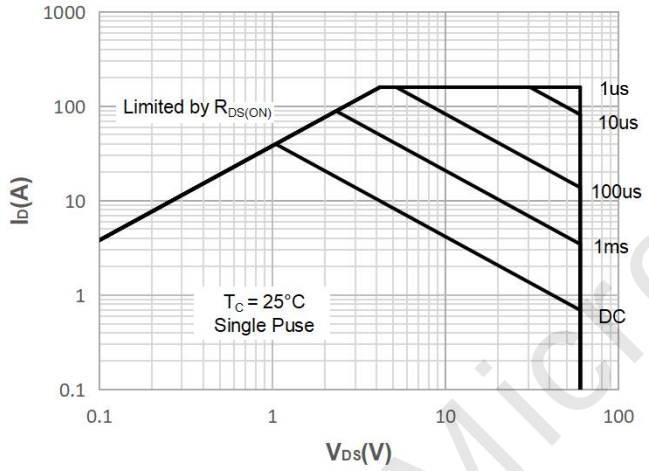


Figure 10: Maximum Continuous Drian Current vs. Case Temperature

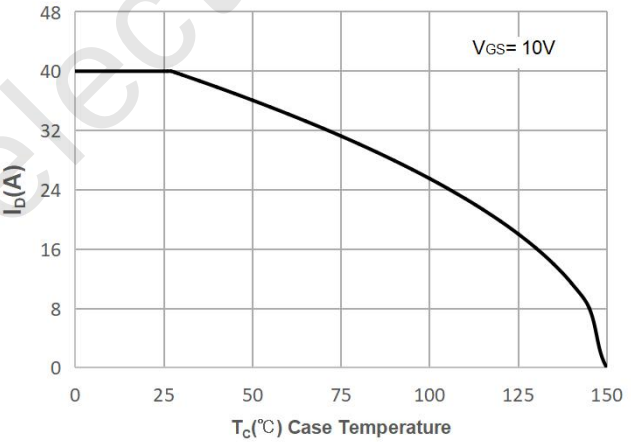


Figure 11: Normalized Maximum Transient Thermal Impedance

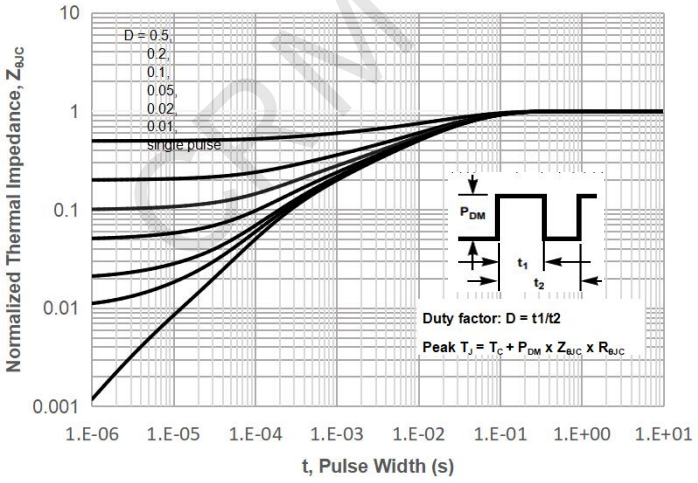
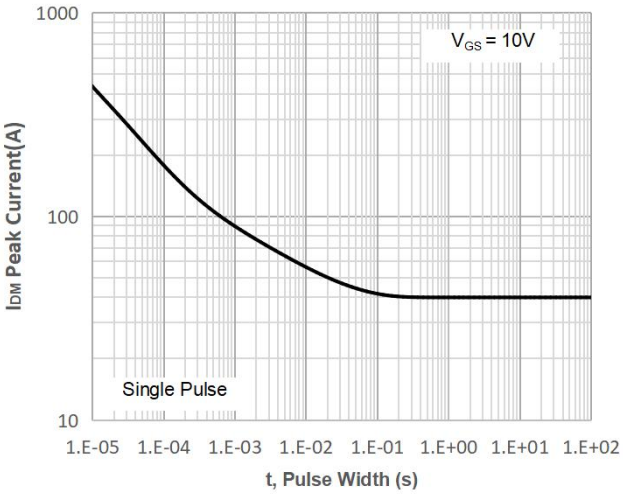


Figure 12: Peak Current Capacity



Test Circuit

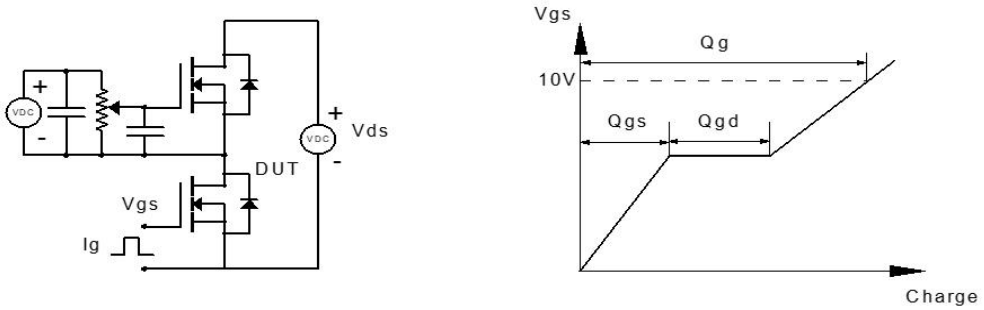


Figure 1: Gate Charge Test Circuit & Waveform

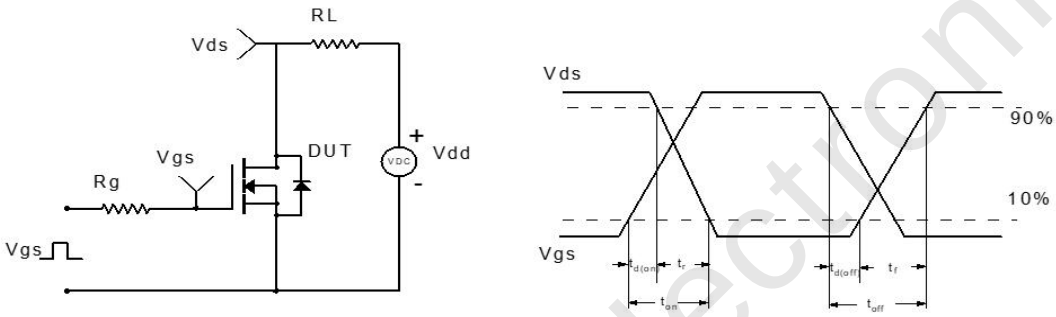


Figure 2: Resistive Switching Test Circuit & Waveform

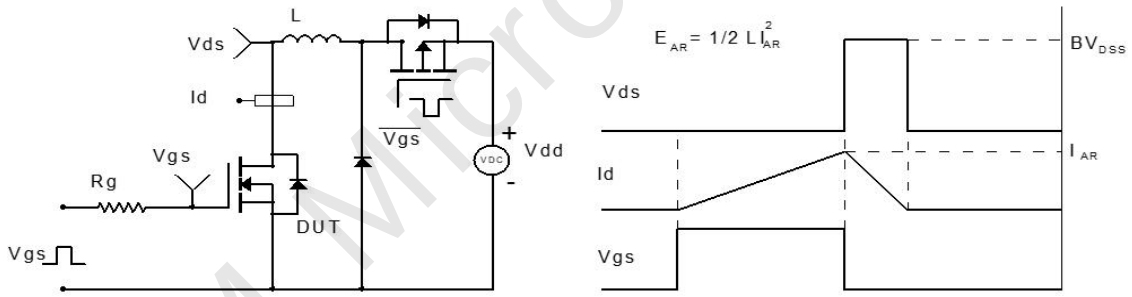


Figure 3: Unclamped Inductive Switching Test Circuit& Waveform

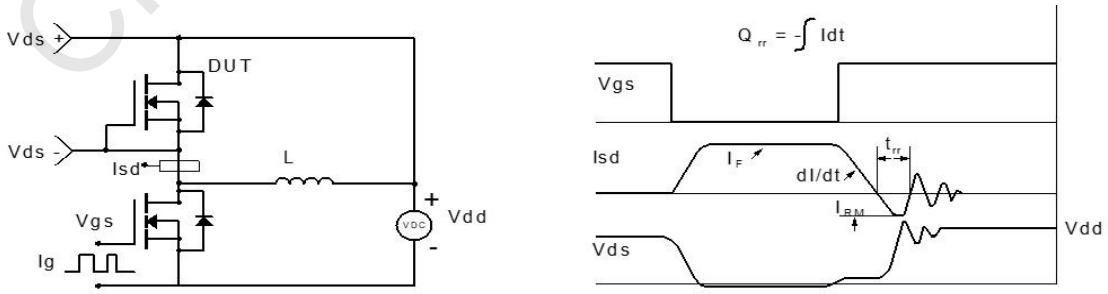
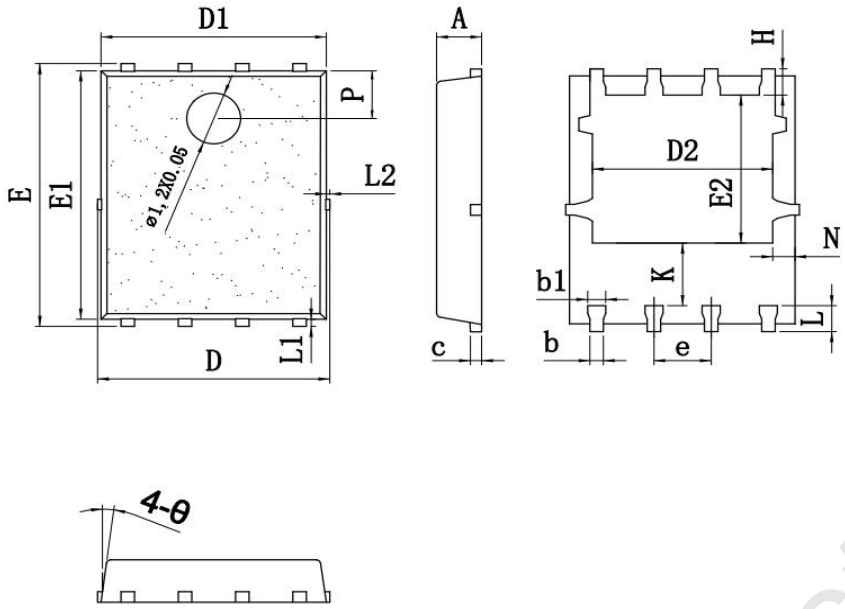


Figure 4: Diode Recovery Test Circuit & Waveform

Package Mechanical Data(PDFN5X6-8L)



SYMBOL	mm		
	MIN	NOM	MAX
*A	0.95	1.00	1.05
*b	0.25	0.30	0.35
*b1	0.30	0.40	0.50
*c	0.20	0.25	0.30
D		5.15BSC	
*D1	4.90	5.00	5.10
D2	3.90	4.01	4.20
*e	1.17	1.27	1.37
E		6.15BSC	
*E1	5.75	5.85	5.95
E2	3.35	3.50	3.65
H	0.51	0.61	0.71
K	1.10	1.35	1.50
L	0.51	0.61	0.71
L1	0.06	0.13	0.20
L2	–	–	0.12
N	0.40	0.50	0.60
P	0.95	1.10	1.25
θ	9°	11°	13°